



General Description

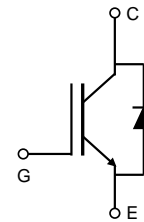
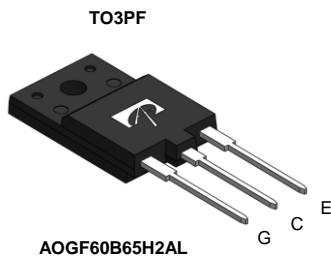
- Latest AlphaGBT (αIGBT) Technology
- 650V breakdown voltage
- Very fast and soft recovery freewheeling diode
- High efficient turn-on di/dt controllability
- Very high switching speed
- Low turn-off switching loss and softness
- Very good EMI behavior

Applications

- Power factor correction
- Very high switching frequency applications

Product Summary

V_{CE}	650V
I_C ($T_C=100^\circ\text{C}$)	60A
$V_{CE(sat)}$ ($T_J=25^\circ\text{C}$)	1.95V



Orderable Part Number	Package Type	Form	Minimum Order Quantity
AOGF60B65H2AL	TO3PF	Tube	480

Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	AOGF60B65H2AL	Units
Collector-Emitter Voltage	V_{CE}	650	V
Gate-Emitter Voltage	V_{GE}	± 30	V
Continuous Collector Current	I_C	$T_C=25^\circ\text{C}$	120 ⁽²⁾
		$T_C=100^\circ\text{C}$	60 ⁽²⁾
Pulsed Collector Current, Limited by T_{Jmax}	I_{CM}	180	A
Turn-Off SOA, $V_{CE} \leq 650\text{V}$, Limited by T_{Jmax}	I_{LM}	180	A
Continuous Diode Forward Current	I_F	$T_C=25^\circ\text{C}$	60 ⁽²⁾
		$T_C=100^\circ\text{C}$	30 ⁽²⁾
Diode Pulsed Current, Limited by T_{Jmax}	I_{FM}	90	A
Power Dissipation	P_D	$T_C=25^\circ\text{C}$	74
		$T_C=100^\circ\text{C}$	29
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$
Maximum Lead Temperature for Soldering Purpose, 1/8" from case for 5 seconds	T_L	300	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	AOGF60B65H2AL	Units
Maximum Junction-to-Ambient	$R_{\theta JA}$	30	$^\circ\text{C/W}$
Maximum IGBT Junction-to-Case	$R_{\theta JC}$	1.7	$^\circ\text{C/W}$
Maximum Diode Junction-to-Case	$R_{\theta JC}$	2.5	$^\circ\text{C/W}$

(1) TO3PF I_C, I_F follows TO247.

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units	
STATIC PARAMETERS							
BV _{CES}	Collector-Emitter Breakdown Voltage	I _C =1mA, V _{GE} =0V, T _J =25°C	650	-	-	V	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} =15V, I _C =60A	T _J =25°C	-	1.95	2.5	V
			T _J =125°C	-	2.45	-	
			T _J =150°C	-	2.58	-	
V _F	Diode Forward Voltage	V _{GE} =0V, I _F =30A	T _J =25°C	-	1.88	2.4	V
			T _J =125°C	-	1.97	-	
			T _J =150°C	-	1.94	-	
V _{GE(th)}	Gate-Emitter Threshold Voltage	V _{CE} =5V, I _C =1mA	-	4.6	-	V	
I _{CES}	Zero Gate Voltage Collector Current	V _{CE} =650V, V _{GE} =0V	T _J =25°C	-	-	10	μA
			T _J =125°C	-	-	1000	
			T _J =150°C	-	-	5000	
I _{GES}	Gate-Emitter Leakage Current	V _{CE} =0V, V _{GE} =±30V	-	-	±100	nA	
g _{FS}	Forward Transconductance	V _{CE} =20V, I _C =60A	-	33	-	S	
DYNAMIC PARAMETERS							
C _{ies}	Input Capacitance	V _{GE} =0V, V _{CC} =25V, f=1MHz	-	2100	-	pF	
C _{oes}	Output Capacitance		-	185	-	pF	
C _{res}	Reverse Transfer Capacitance		-	65	-	pF	
Q _g	Total Gate Charge	V _{GE} =15V, V _{CC} =520V, I _C =60A	-	84	-	nC	
Q _{ge}	Gate to Emitter Charge		-	21	-	nC	
Q _{gc}	Gate to Collector Charge		-	38	-	nC	
R _g	Gate Resistance	V _{GE} =0V, V _{CC} =0V, f=1MHz	-	15	-	Ω	
SWITCHING PARAMETERS, (Load Inductive, T_J=25°C)							
t _{D(on)}	Turn-On Delay Time	T _J =25°C V _{GE} =15V, V _{CC} =400V, I _C =60A, R _G =5Ω	-	35	-	ns	
t _r	Turn-On Rise Time		-	80	-	ns	
t _{D(off)}	Turn-Off Delay Time		-	168	-	ns	
t _f	Turn-Off Fall Time		-	76	-	ns	
E _{on}	Turn-On Energy		-	2.36	-	mJ	
E _{off}	Turn-Off Energy		-	1.17	-	mJ	
E _{total}	Total Switching Energy		-	3.54	-	mJ	
t _{rr}	Diode Reverse Recovery Time	T _J =25°C I _F =30A, di/dt=200A/μs, V _{CC} =400V	-	318	-	ns	
Q _{rr}	Diode Reverse Recovery Charge		-	0.8	-	μC	
I _{rm}	Diode Peak Reverse Recovery Current		-	6.0	-	A	
SWITCHING PARAMETERS, (Load Inductive, T_J=150°C)							
t _{D(on)}	Turn-On Delay Time	T _J =150°C V _{GE} =15V, V _{CC} =400V, I _C =60A, R _G =5Ω	-	33	-	ns	
t _r	Turn-On Rise Time		-	80	-	ns	
t _{D(off)}	Turn-Off Delay Time		-	195	-	ns	
t _f	Turn-Off Fall Time		-	75	-	ns	
E _{on}	Turn-On Energy		-	2.53	-	mJ	
E _{off}	Turn-Off Energy		-	1.51	-	mJ	
E _{total}	Total Switching Energy		-	4.04	-	mJ	
t _{rr}	Diode Reverse Recovery Time	T _J =150°C I _F =30A, di/dt=200A/μs, V _{CC} =400V	-	427	-	ns	
Q _{rr}	Diode Reverse Recovery Charge		-	1.6	-	μC	
I _{rm}	Diode Peak Reverse Recovery Current		-	7.5	-	A	

APPLICATIONS OR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS ARE NOT AUTHORIZED. AOS DOES NOT ASSUME ANY LIABILITY ARISING OUT OF SUCH APPLICATIONS OR USES OF ITS PRODUCTS. AOS RESERVES THE RIGHT TO IMPROVE PRODUCT DESIGN, FUNCTIONS AND RELIABILITY WITHOUT NOTICE.

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

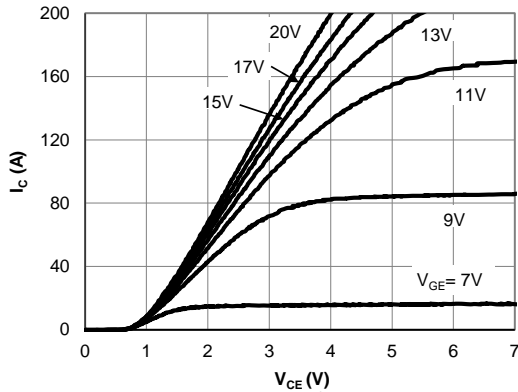


Figure 1: Output Characteristic
($T_j=25^\circ\text{C}$)

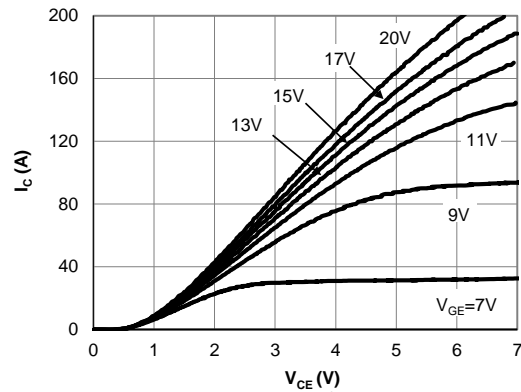


Figure 2: Output Characteristic
($T_j=150^\circ\text{C}$)

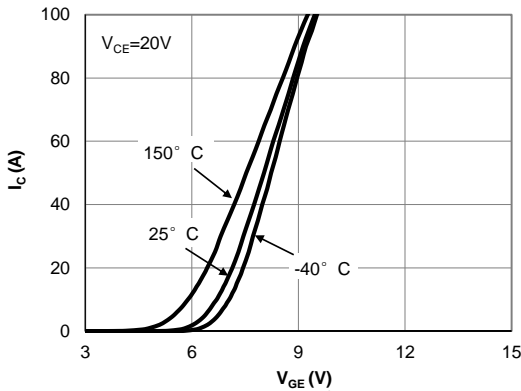


Figure 3: Transfer Characteristic

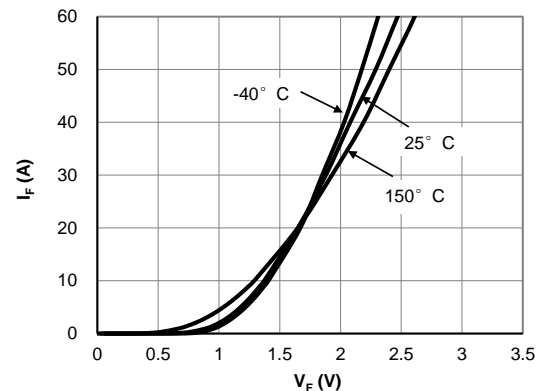


Figure 4: Diode Characteristic

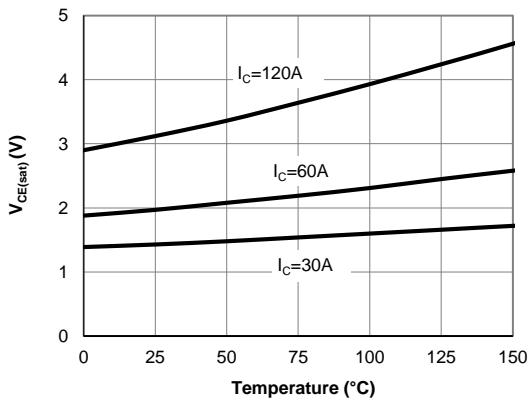


Figure 5: Collector-Emitter Saturation Voltage vs. Junction Temperature

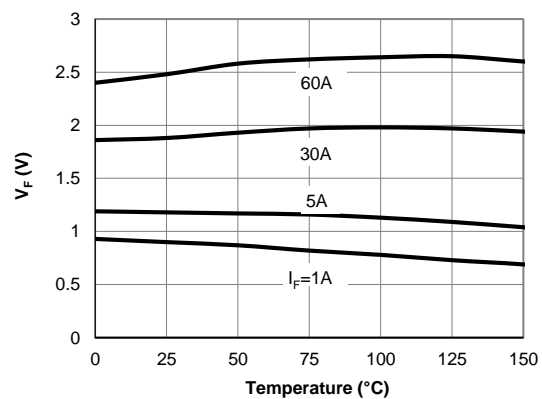


Figure 6: Diode Forward voltage vs. Junction Temperature

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

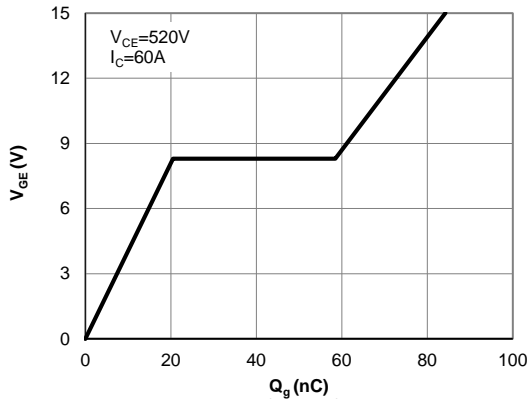


Figure 7: Gate-Charge Characteristics

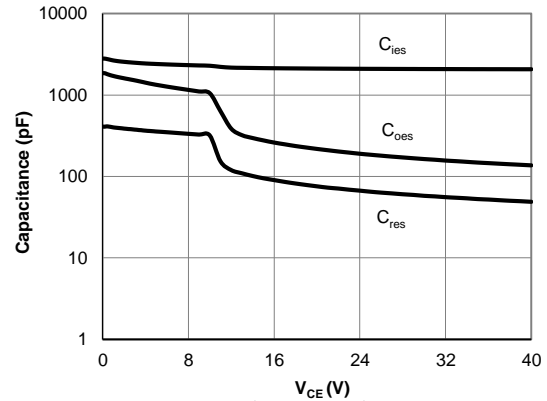


Figure 8: Capacitance Characteristic

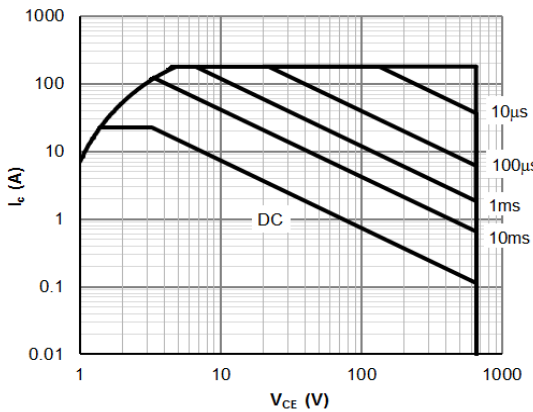


Figure 9: Forward Bias Safe Operating Area
($T_C=25^{\circ}\text{C}$, $V_{GE}=15\text{V}$)

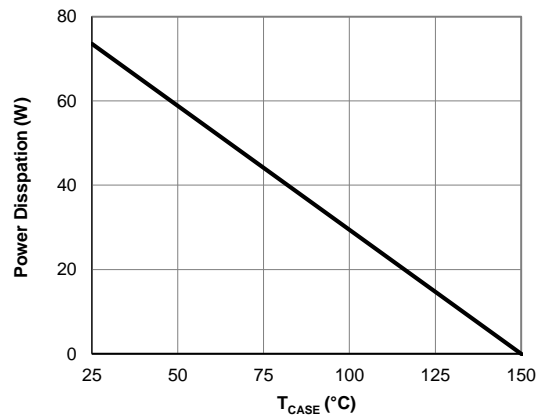


Figure 10: Power Dissipation as a Function of Case

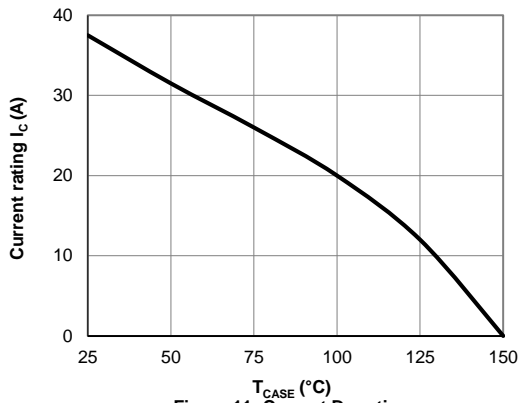


Figure 11: Current De-rating

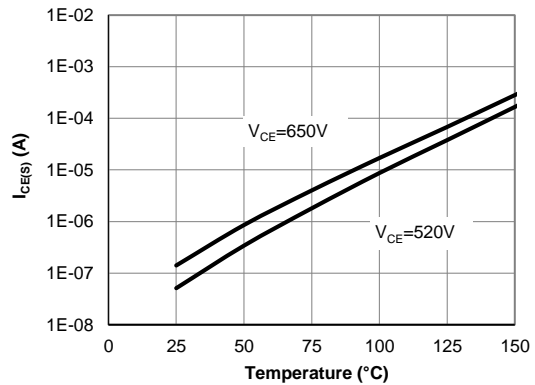


Figure 12: Diode Reverse Leakage Current vs. Junction Temperature

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

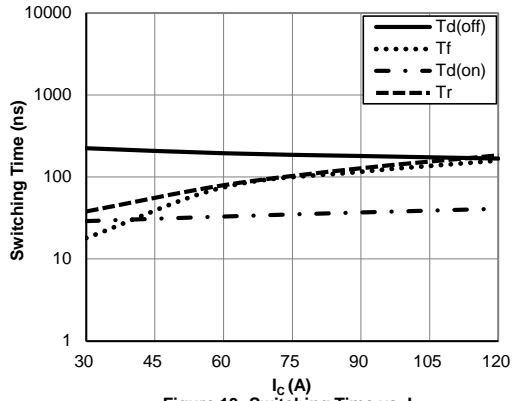


Figure 13: Switching Time vs. I_C
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $R_g=5\Omega$)

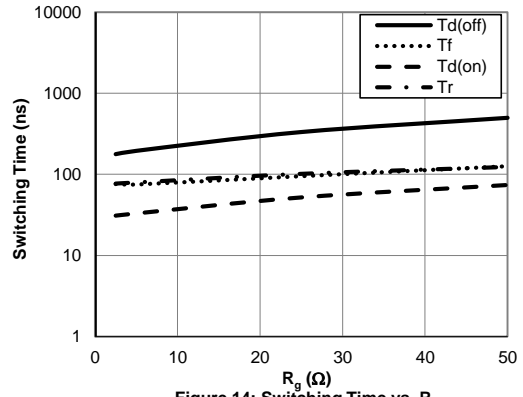


Figure 14: Switching Time vs. R_g
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=60\text{A}$)

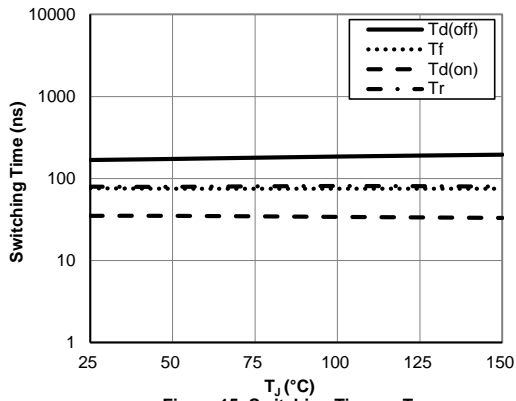


Figure 15: Switching Time vs. T_J
($V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=60\text{A}$, $R_g=5\Omega$)

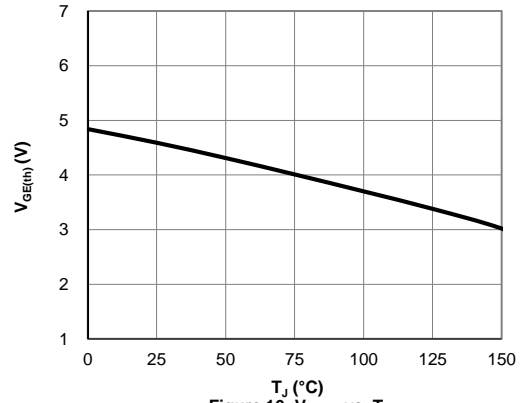


Figure 16: $V_{GE(th)}$ vs. T_J

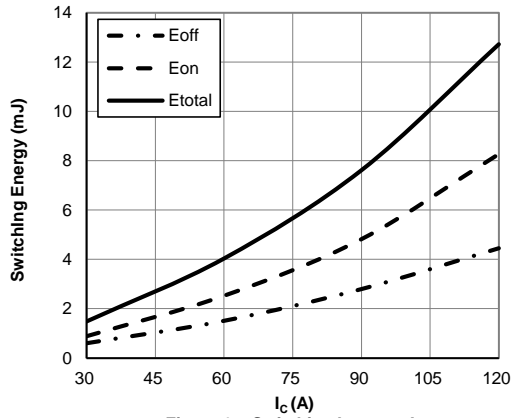


Figure 17: Switching Loss vs. I_C
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $R_g=5\Omega$)

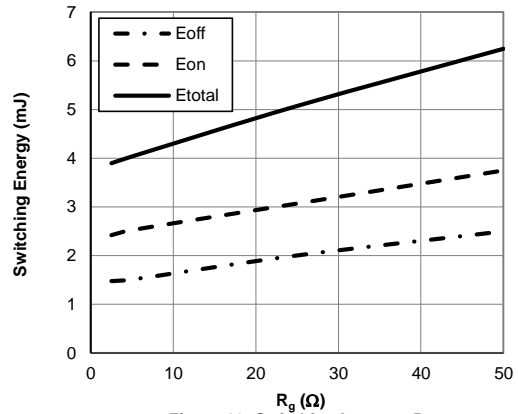


Figure 18: Switching Loss vs. R_g
($T_J=150^\circ\text{C}$, $V_{GE}=15\text{V}$, $V_{CE}=400\text{V}$, $I_C=60\text{A}$)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

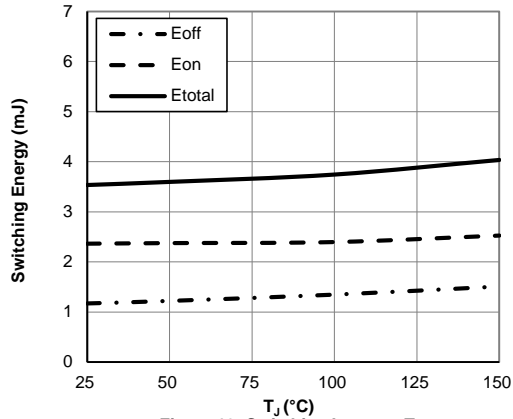


Figure 19: Switching Loss vs. T_j
($V_{GE}=15V$, $V_{CE}=400V$, $I_C=60A$, $R_g=5\Omega$)

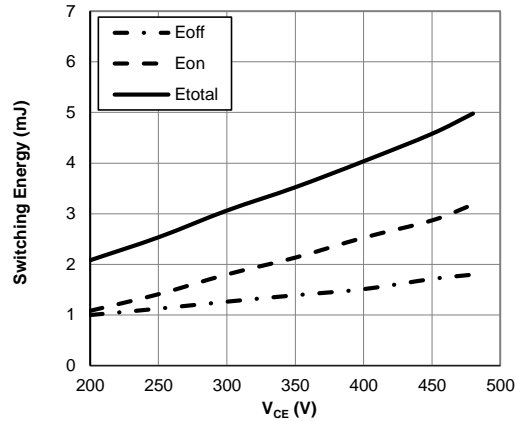


Figure 20: Switching Loss vs. V_{CE}
($T_j=150^\circ C$, $V_{GE}=15V$, $I_C=60A$, $R_g=5\Omega$)

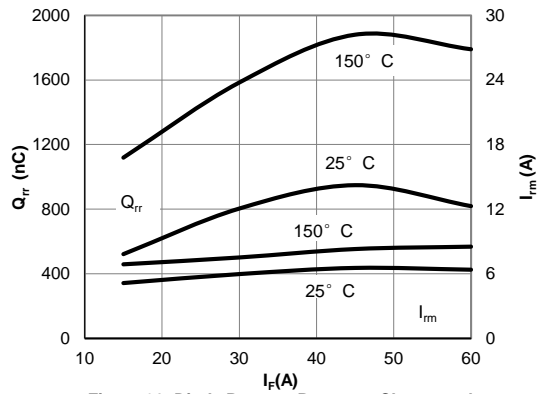


Figure 21: Diode Reverse Recovery Charge and Peak Current vs. Conduction Current
($V_{GE}=15V$, $V_{CE}=400V$, $di/dt=200A/\mu s$)

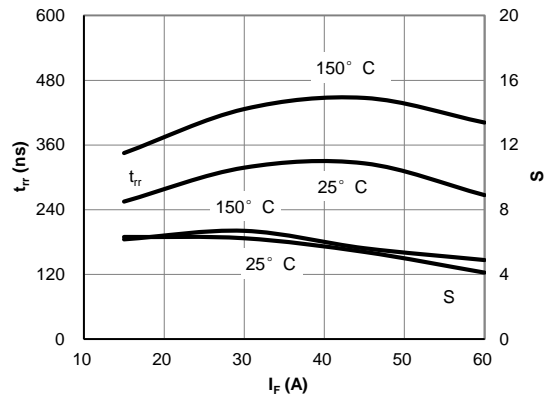


Figure 22: Diode Reverse Recovery Time and Softness Factor vs. Conduction Current
($V_{GE}=15V$, $V_{CE}=400V$, $di/dt=200A/\mu s$)

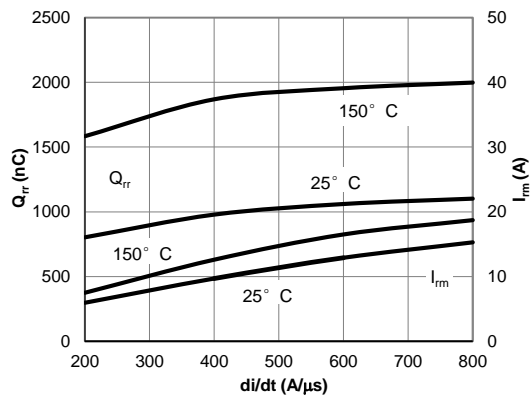


Figure 23: Diode Reverse Recovery Charge and Peak Current vs. di/dt
($V_{GE}=15V$, $V_{CE}=400V$, $I_F=30A$)

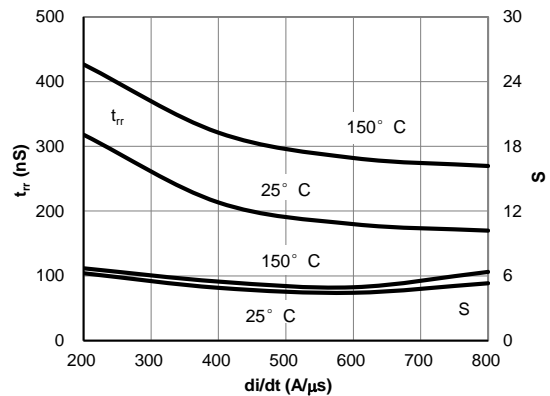


Figure 24: Diode Reverse Recovery Time and Softness Factor vs. di/dt
($V_{GE}=15V$, $V_{CE}=400V$, $I_F=30A$)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

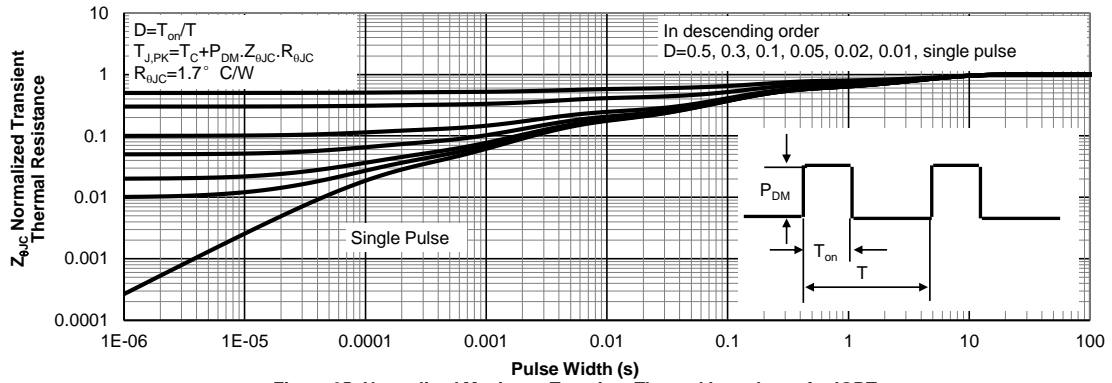


Figure 25: Normalized Maximum Transient Thermal Impedance for IGBT

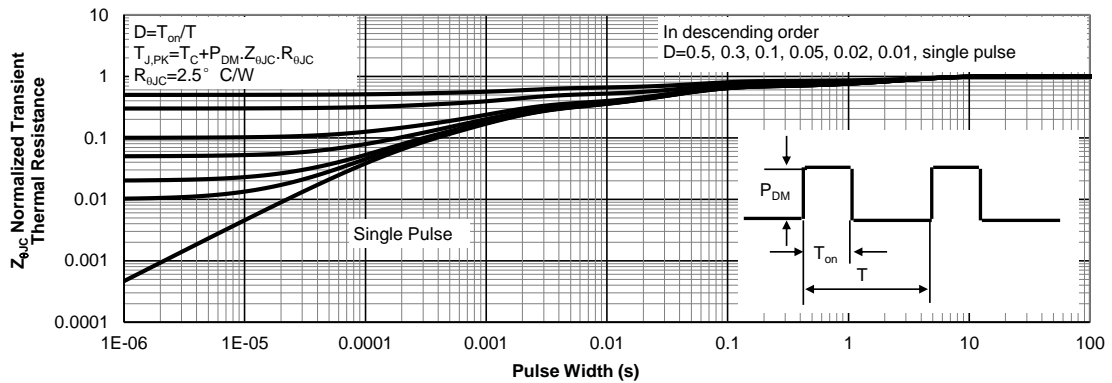


Figure 26: Normalized Maximum Transient Thermal Impedance for Diode

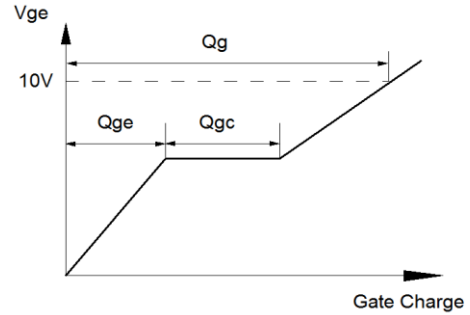
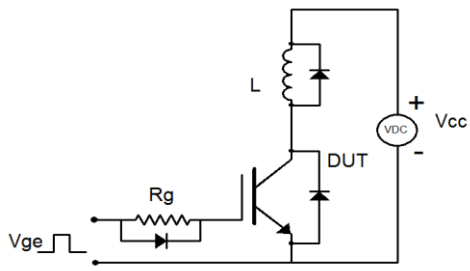


Figure A: Gate Charge Test Circuit & Waveforms

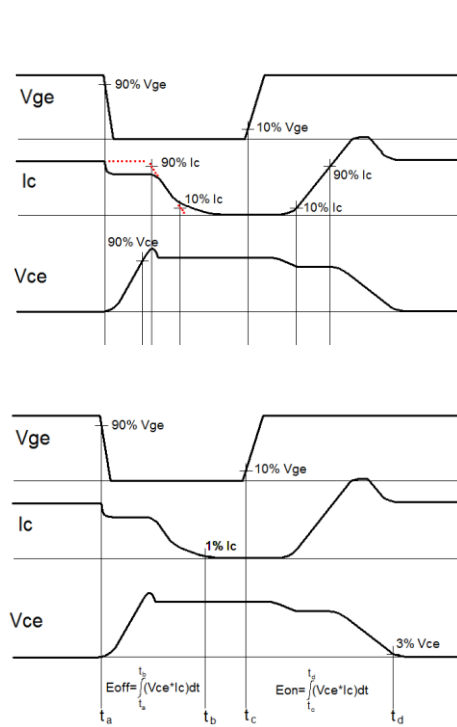
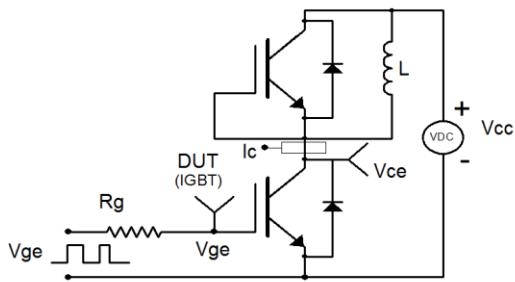


Figure B: Inductive Switching Test Circuit & Waveforms

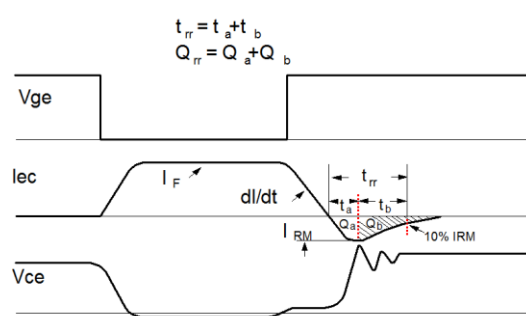
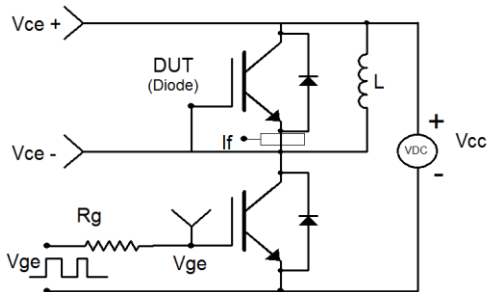


Figure C: Diode Recovery Test Circuit & Waveforms

单击下面可查看定价，库存，交付和生命周期等信息

[>>AOS\(万代\)](#)